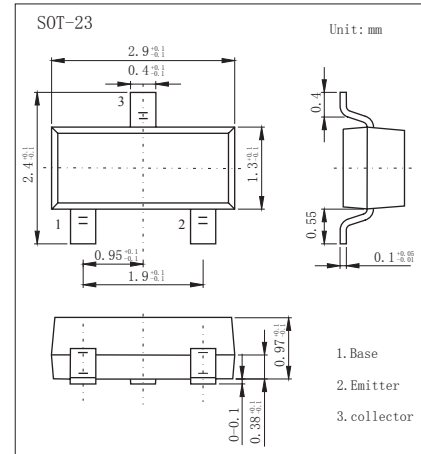


NPN Transistors

MMBT5551 (KMBT5551)

■ Features

- High Voltage Transistors
- Pb-Free Packages are Available



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	180	V
Collector-emitter voltage	V _{CEO}	160	V
Emitter-base voltage	V _{EBO}	6	V
Collector current-continuous	I _C	0.6	A
Collector Power Dissipation	P _C	300	mW
Junction and storage temperature	T _J , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = 100uA, I _E = 0	180			V
Collector-emitter breakdown voltage *	V _{CEO}	I _C = 1.0 mA, I _B = 0	160			V
Emitter-base breakdown voltage	V _{EBO}	I _E = 10uA, I _C = 0	6			V
Collector cutoff current	I _{CBO}	V _{CB} = 120 V, I _E = 0			50	nA
Emitter cutoff current	I _{EBO}	V _{EB} = 4.0 V, I _C = 0			50	nA
DC current gain *	h _{FE}	I _C = 1.0 mA, V _{CE} = 5 V	80			
		I _C = 10 mA, V _{CE} = 5 V	100		300	
		I _C = 50 mA, V _{CE} = 5 V	50			
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = 50 mA, I _B = 5.0 mA			0.5	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = 50 mA, I _B = 5.0 mA			1.0	V
Transiston frequency	f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100			MHz

* Pulse Test: Pulse Width = 300 μs, Duty Cycle=2.0%.

■ Classification of h_{FE}(2)

Type	MMBT5551	MMBT5551-L	MMBT5551-H
Range	100-300	100-200	200-300
Marking	G1		

MMBT5551 (KMBT5551)

Typical Characteristics

